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# 0.01 GHz to 10 GHz, MMIC, GaAs, pHEMT RF Gain Block

Enhanced Product HMC788A-EP

#### **FEATURES**

Gain: 14 dB typical

Operational frequency range: 0.01 GHz to 10 GHz

Input/output internally matched to 50  $\Omega$ 

**High input linearity** 

1 dB compression (P1dB): 20 dBm typical

Output third-order intercept (OIP3): 33 dBm typical

Supply voltage: 5 V typical

2 mm × 2 mm, 6-lead lead frame chip scale package

### **ENHANCED PRODUCT FEATURES**

Supports defense and aerospace applications (AQEC standard)

Extended industrial temperature range: -55°C to +105°C

Controlled manufacturing baseline

One assembly/test site
One fabrication site

Enhanced product change notification

Qualification data available on request

#### **APPLICATIONS**

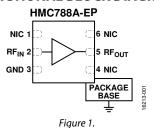
Cellular, 3G, LTE, WiMAX, and 4G LO driver applications Microwave radio Test and measurement equipment Ultra wideband (UWB) communications

## **GENERAL DESCRIPTION**

The HMC788A-EP is a 0.01 GHz to 10 GHz, gain block, monolithic microwave integrated circuit (MMIC) amplifier using gallium arsenide (GaAs) and pseudomorphic high electron mobility transistor (pHEMT) technology.

This 2 mm  $\times$  2 mm LFCSP amplifier can be used as either a cascadable 50  $\Omega$  gain stage, or to drive the local oscillator (LO) port of many of the single and double balanced mixers from Analog Devices, Inc. with up to 20 dBm output power.

#### **FUNCTIONAL BLOCK DIAGRAM**



The HMC788A-EP offers 14 dB of gain and an OIP3 of 33 dBm while requiring only 76 mA from a 5 V supply.

The Darlington feedback pair exhibits reduced sensitivity to normal process variations and yields excellent gain stability over temperature while requiring a minimal number of external bias components.

Additional application and technical information can be found in the HMC788A data sheet.

# **TABLE OF CONTENTS**

reatures	
Enhanced Product Features	. 1
Applications	. 1
Functional Block Diagram	. 1
General Description	. 1
Revision History	. 2
Specifications	. 3
Electrical Specifications	. 3
Absolute Maximum Ratings	

I hermal Resistance	4
Power Derating Curves	
ESD Caution	
Pin Configuration and Function Descriptions	
Interface Schematics	
Typical Performance Characteristics	
Outline Dimensions	8
Ordering Guide	

## **REVISION HISTORY**

10/2017—Revision 0: Initial Version

Enhanced Product HMC788A-EP

# **SPECIFICATIONS**

# **ELECTRICAL SPECIFICATIONS**

Collector bias voltage ( $V_{CC}$ ) = 5 V, case temperature ( $T_{CASE}$ ) = 25°C, 6.35  $\mu$ H external inductor between  $V_{CC}$  and radio frequency output (RF<sub>OUT</sub>), 50  $\Omega$  system, unless otherwise noted.

Table 1.

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions/Comments
OVERALL FUNCTION						
Frequency Range		0.01		10	GHz	
Gain		12	14		dB	0.01 GHz to 6.0 GHz
		9	12		dB	6.0 GHz to 10.0 GHz
Gain Variation Over Temperature			0.004		dB/°C	0.01 GHz to 6.0 GHz
			0.007		dB/°C	6.0 GHz to 10.0 GHz
Reverse Isolation			23		dB	0.01 GHz to 6.0 GHz
			20		dB	6.0 GHz to 10 GHz
RADIO FREQUENCY (RF) INPUT INTERFACE						
Input Return Loss			16		dB	0.01 GHz to 6.0 GHz
			9		dB	6.0 GHz to 10.0 GHz
RF OUTPUT INTERFACE						
Output Power for 1 dB Compression	P1dB	18	20		dBm	0.01 GHz to 6.0 GHz
		15	18		dBm	6.0 GHz to 10.0 GHz
Output Return Loss			9		dB	0.01 GHz to 6.0 GHz
			12		dB	6.0 GHz to 10.0 GHz
DISTORTION AND NOISE						
Output Third-Order Intercept	OIP3		33		dBm	0.01 GHz to 6.0 GHz
			30		dBm	6.0 GHz to 10.0 GHz
Noise Figure	NF		6		dB	0.01 GHz to 6.0 GHz
			7		dB	6.0 GHz to 10.0 GHz
POWER INTERFACE						
Supply Voltage		4.5	5	5.5	V	
Supply Current	lcc	60	65		mA	$V_{CC} = 4.5 V$
			76		mA	$V_{CC} = 5 V$
			87	90	mA	$V_{CC} = 5.5 V$

# **ABSOLUTE MAXIMUM RATINGS**

Table 2.

Parameter	Rating
V <sub>CC</sub>	7 V
$RF_{IN}$ ( $V_{CC} = 5 V$ )	15 dBm
Continuous Power Dissipation, PDISS <sup>1</sup>	
$T_{CASE} = 85^{\circ}C$	0.55 W
$T_{CASE} = 105^{\circ}C$	0.38 W
Junction (T <sub>J</sub> ) Temperature	150°C
Operating (T <sub>OPR</sub> ) Temperature Range	−55°C to +105°C
Storage Temperature Range	−65°C to +150°C
Electrostatic Discharge (ESD) Sensitivity, Human Body Model (HBM)	Class 1A

<sup>&</sup>lt;sup>1</sup> For maximum power dissipation vs. case temperature, see Figure 2.

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

## THERMAL RESISTANCE

Thermal performance is directly linked to printed circuit board (PCB) design and operating environment. Careful attention to PCB thermal design is required.

 $\theta_{JC}$  is the junction to case thermal resistance.

**Table 3. Thermal Resistance** 

Package Type	θ <sub>JC</sub>	Unit	
CP-6-10 <sup>1</sup>	118.0	°C/W	

<sup>&</sup>lt;sup>1</sup>Thermal impedance simulated values are based on a JEDEC 2S2P thermal test board with nine thermal vias. See JEDEC JESD51.

#### **POWER DERATING CURVES**

Figure 2 shows the maximum power dissipation vs. case temperature.

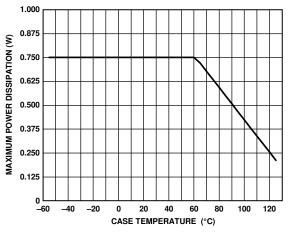


Figure 2. Maximum Power Dissipation vs. Case Temperature

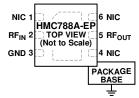
## **ESD CAUTION**



**ESD (electrostatic discharge) sensitive device.**Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

**Enhanced Product** HMC788A-EP

# PIN CONFIGURATION AND FUNCTION DESCRIPTIONS



- NOTES

  1. NIC = NOT INTERNALLY CONNECTED.
  THE PINS ARE NOT CONNECTED INTERNALLY; HOWEVER, ALL DATA SHOWN HEREIN WAS MEASURED WITH THESE PINS CONNECTED TO GND EXTERNALLY.

  2. EXPOSED PAD. THE EXPOSED PAD MUST BE CONNECTED TO GND FOR PROPER OPERATION.

Figure 3. Pin Configuration

**Table 4. Pin Function Descriptions** 

Pin No.	Mnemonic	Description
1, 4, 6	NIC	Not Internally Connected. The pins are not connected internally; however, all data shown herein was measured with these pins connected to GND externally.
2	RF <sub>IN</sub>	RF Input. This pin is dc-coupled and ac matched to $50 \Omega$ . An external dc blocking capacitor is required on this pin.
3	GND	Ground. This pin must be connected to ground.
5	RFout	RF Output. This pin is ac matched to $50\Omega$ and supplies dc bias for the output stage.
	EPAD	Exposed Pad. The exposed pad must be connected to GND for proper operation.

## **INTERFACE SCHEMATICS**

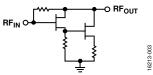


Figure 4.  $RF_{IN}$ ,  $RF_{OUT}$  Interface Schematic



Figure 5. GND Interface Schematic

# TYPICAL PERFORMANCE CHARACTERISTICS

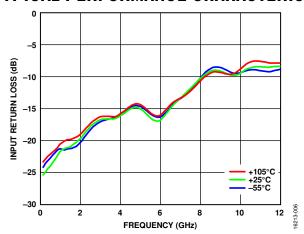


Figure 6. Input Return Loss vs. Frequency at Various Temperatures

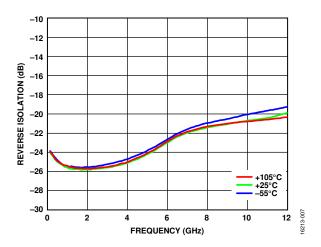


Figure 7. Reverse Isolation vs. Frequency at Various Temperatures

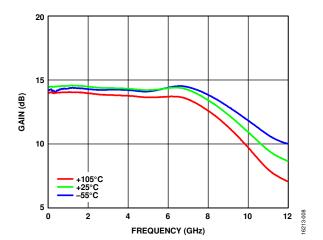


Figure 8. Gain vs. Frequency at Various Temperatures

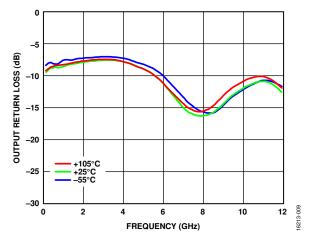


Figure 9. Output Return Loss vs. Frequency at Various Temperatures

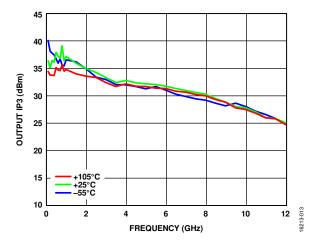


Figure 10. Output IP3 vs. Frequency at Various Temperatures; 5 dBm per Tone Output Power

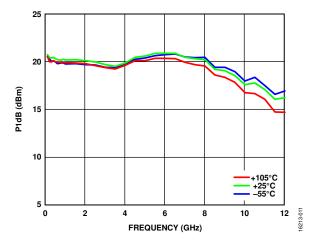


Figure 11. P1dB vs. Frequency at Various Temperatures

Enhanced Product HMC788A-EP

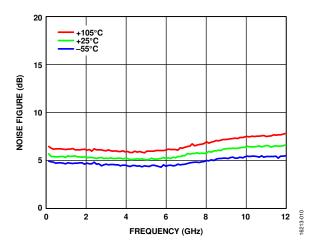


Figure 12. Noise Figure vs. Frequency at Various Temperatures

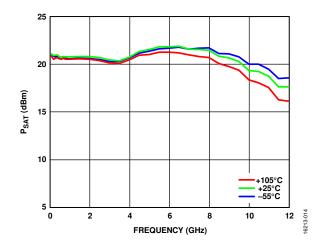


Figure 13. Saturation Power (P<sub>SAT</sub>) vs. Frequency at Various Temperatures

Rev. 0 | Page 7 of 8

# **OUTLINE DIMENSIONS**

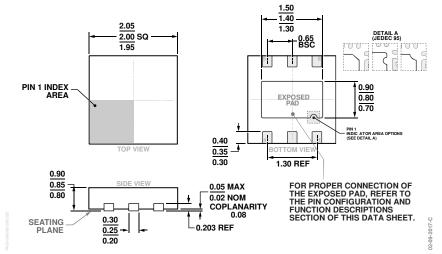


Figure 14. 6-Lead Lead Frame Chip Scale Package [LFCSP] 2 mm × 2 mm Body and 0.85 mm Package Height (CP-6-10) Dimensions shown in millimeters

## **ORDERING GUIDE**

Model <sup>1</sup>	Temperature Range	MSL Rating <sup>2</sup> Package Description		Package Option
HMC788ACPSZ-EP-PT	−55°C to +105°C	MSL1	6-Lead Lead Frame Chip Scale Package [LFCSP]	CP-6-10
HMC788ACPSZ-EP-R7	−55°C to +105°C	MSL1	6-Lead Lead Frame Chip Scale Package [LFCSP]	CP-6-10

<sup>&</sup>lt;sup>1</sup> All models are RoHS Compliant.

 $<sup>^{\</sup>rm 2}\, {\rm See}$  the Absolute Maximum Ratings section.